

5/20/14

Page 1 of 2

FORM PTO-1449

## INFORMATION DISCLOSURE STATEMENT

ATTY. DOCKET NO.

1875.0220001

APPLICATION NO.

To Be Assigned

FIRST NAMED INVENTOR

Vincent Chen

FILING DATE

Herewith

ART UNIT

To Be Assigned

## U.S. PATENT DOCUMENTS

EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB- CLASS	FILING DATE
<i>D</i>	AA1	4,173,791	11/1979	Bell, Antony G.	<u>          </u>	<u>          </u>	
<i>D</i>	AB1	4,499,557	02/1985	Holmberg <i>et al.</i>	<u>          </u>	<u>          </u>	
<i>2</i>	AC1	5,163,180	11/1992	Eltoukhy <i>et al.</i>	<u>          </u>	<u>          </u>	
<i>D</i>	AD1	5,480,828	01/1996	Hsu <i>et al.</i>	<u>          </u>	<u>          </u>	
<i>D</i>	AE1	5,742,555	04/1998	Marr <i>et al.</i>	<u>          </u>	<u>          </u>	
<i>D</i>	AF1	5,748,025	05/1998	Ng <i>et al.</i>	<u>          </u>	<u>          </u>	
<i>D</i>	AG1	5,834,824	11/1998	Shepherd <i>et al.</i>	<u>          </u>	<u>          </u>	
<i>D</i>	AH1	5,886,392	03/1999	Schuegraf	<u>          </u>	<u>          </u>	
<i>D</i>	AI1	5,949,712	09/1999	Rao <i>et al.</i>	<u>          </u>	<u>          </u>	
<i>2</i>	AJ1	6,044,012	03/2000	Rao <i>et al.</i>	<u>          </u>	<u>          </u>	
<i>D</i>	AK1	6,096,580	08/2000	Iyer <i>et al.</i>	<u>          </u>	<u>          </u>	

## FOREIGN PATENT DOCUMENTS

EXAMINER INITIAL		DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUB- CLASS	TRANSLATION
	AL1						Yes No
	AM1						Yes No
	AN1						Yes No
	AO1						Yes No
	AP1						Yes No

## OTHER (Including Author, Title, Date, Pertinent Pages, etc.)

<i>D</i>	AR	1	Clark, Lawrence T., "A High-Voltage Output Buffer Fabricated on a 2V CMOS Technology," <i>Symposium on VLSI Circuits Digest of Technical Papers</i> , pp. 61-62, 1999.				
<i>D</i>	AS	1	International Search Report for PCT/US01/48853, 5 pages, July 31, 2002.				
<i>D</i>	AT	1	Schroder, Dieter K., "Semiconductor Material and Device Characterization," Fig. E6.5(a), Oxide failure modes, John Wiley & Sons, Inc., 2 <sup>nd</sup> Edition, p. 391, 1998.				

EXAMINER

DATE CONSIDERED

2/5/08

EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to Applicant.

5/20/04

FORM PTO-1449  <b>INFORMATION DISCLOSURE STATEMENT</b>	ATTY. DOCKET NO. 1875.0220001 FIRST NAMED INVENTOR Vincent Chen FILING DATE Herewith	APPLICATION NO. To Be Assigned ART UNIT To Be Assigned
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**U.S. PATENT DOCUMENTS**

EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB-CLASS	FILING DATE
	AA2	6,096,610	08/2000	Alavi <i>et al.</i>			
	AB2	6,184,726 B1	02/2001	Haebler <i>et al.</i>			06/29/1999
	AC2	6,266,269 B1	07/2001	Karp <i>et al.</i>			06/07/2000
	AD2	6,351,425 B1	02/2002	Porter, Stephen R.			12/07/2000
	AE2	6,477,094 B2	11/2002	Kim <i>et al.</i>			12/18/2000
	AF2	6,549,458 B1	04/2003	Rao <i>et al.</i>			10/25/2001
	AG2						
	AH2						
	AI2						
	AJ2						
	AK2						

**FOREIGN PATENT DOCUMENTS**

EXAMINER INITIAL		DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUB-CLASS	TRANSLATION
	AL2						Yes No
	AM2						Yes No
	AN2						Yes No
	AO2						Yes No
	AP2						Yes No

**OTHER (Including Author, Title, Date, Pertinent Pages, etc.)**

	AR	2	Schroder, Dieter K., "Semiconductor Material and Device Characterization," Fig. 6.40, Charge-to-breakdown as a function of oxide thickness, John Wiley & Sons, Inc., 2 <sup>nd</sup> Edition, p. 397, 1998.
	AS	2	Shi, Y., <i>et al.</i> , "Polarity-Dependent Tunneling Current and Oxide Breakdown in Dual-Gate CMOSFET's," <i>IEEE Electron Device Letters</i> , Volume 19, No. 10, pp. 391-393, October 1998.
	AT	2	

EXAMINER	DATE CONSIDERED 2/5/00
EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to Applicant.	

**FIRST SUPPLEMENTAL**  
**INFORMATION DISCLOSURE STATEMENT**

**APPLICATION NO.**  
**10/849,295**

**FILING DATE**  
May 20, 2004

ART UNIT  
2815

EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB- CLASS	FILING DATE
P	AG2	6,445,619 B1	09/2002	Mihnea et al.			08/01/2001
D	AH2	6,566,189 B2	05/2003	Joo et al.			07/02/2001

EXAMINER INITIAL		DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUB- CLASS	TRANSLATION
							Yes
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							No
							Yes
							No

DATE CONSIDERED

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